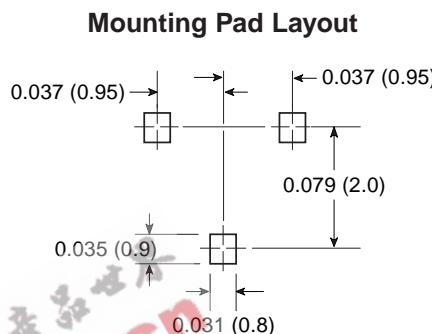
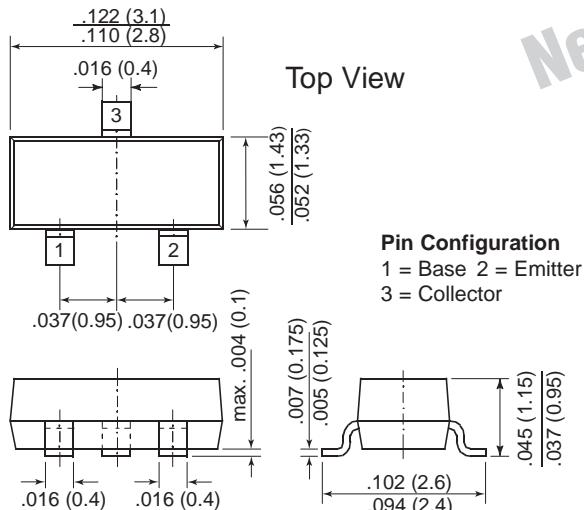


Small Signal Transistor (NPN)

TO-236AB (SOT-23)


Mechanical Data

Case: SOT-23 Plastic Package

Weight: approx. 0.008g

Marking BCX70G = AG
Code: BCX70H = AH
BCX70J = AJ
BCX70K = AK

Packaging Codes/Options:

E8/10K per 13" reel (8mm tape), 30K/box
E9/3K per 7" reel (8mm tape), 30K/box

Features

- NPN Silicon Epitaxial Planar Transistors for switching and AF amplifier applications.
- Suited for low level, low noise, low frequency applications in hybrid circuits.
- Low current, low voltage.
- As complementary types, BCX71 Series PNP transistors are recommended.

Maximum Ratings & Thermal Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	45	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	200	mA
Peak Base Current	I _B	50	mA
Power Dissipation	P _{tot}	250	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	500 ⁽¹⁾	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-65 to +150	°C

Note: (1) Mounted on FR-4 printed-circuit board.

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DC Current Gain	h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 10 \mu\text{A}$	—	—	—	
		$V_{CE} = 5 \text{ V}, I_C = 10 \mu\text{A}$	30	—	—	
		$V_{CE} = 5 \text{ V}, I_C = 10 \mu\text{A}$	40	—	—	
		$V_{CE} = 5 \text{ V}, I_C = 10 \mu\text{A}$	100	—	—	
		$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$	120	—	220	
		$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$	180	—	310	
		$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$	250	—	460	
		$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$	380	—	630	
		$V_{CE} = 1 \text{ V}, I_C = 50 \text{ mA}$	50	—	—	
		$V_{CE} = 1 \text{ V}, I_C = 50 \text{ mA}$	70	—	—	
		$V_{CE} = 1 \text{ V}, I_C = 50 \text{ mA}$	90	—	—	
		$V_{CE} = 1 \text{ V}, I_C = 50 \text{ mA}$	100	—	—	
Collector-Emitter Saturation Voltage	V_{CEsat}	$I_C = 10 \text{ mA}, I_B = 0.25 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.25 \text{ mA}$	50 100	—	350 550	mV
Base-Emitter Saturation Voltage	V_{BEsat}	$I_C = 10 \text{ mA}, I_B = 0.25 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 1.25 \text{ mA}$	600 700	—	850 1050	mV
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$ $V_{CE} = 5 \text{ V}, I_C = 10 \mu\text{A}$ $V_{CE} = 1 \text{ V}, I_C = 50 \text{ mA}$	550 — —	650 520 780	750 — —	mV
Collector Cut-off Current	I_{CBO}	$V_{CB} = 45 \text{ V}, V_{BE} = 0 \text{ V}$ $V_{CB} = 45 \text{ V}, V_{BE} = 0 \text{ V}$ $T_A = 150^\circ\text{C}$	— — —	— — —	20 20	nA μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 4 \text{ V}, I_C = 0$	—	—	20	nA
Gain-Bandwidth Product	f_T	$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}$ $f = 100 \text{ MHz}$	100	250	—	MHz
Collector-Base Capacitance	C_{CBO}	$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, I_E = 0$	—	2.5	—	pF
Emitter-Base Capacitance	C_{EBO}	$V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, I_C = 0$	—	8	—	pF
Noise Figure	F	$V_{CE} = 5 \text{ V}, I_C = 200 \mu\text{A}$, $R_S = 2 \text{ k}\Omega$, $f = 1 \text{ kHz}$, $B = 200 \text{ Hz}$	—	2	6	dB
Small Signal Current Gain	h_{fe}	$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$, $f = 1.0 \text{ kHz}$	— — — —	200 260 330 520	—	
Turn-on Time at $R_L = 990\Omega$ (see fig. 1)	t_{on}	$V_{CC} = 10 \text{ V}, I_C = 10 \text{ mA}$, $I_{B(on)} = -I_{B(off)} = 1 \text{ mA}$	—	85	150	ns
Turn-off Time at $R_L = 990\Omega$ (see fig. 1)	t_{off}	$V_{CC} = 10 \text{ V}, I_C = 10 \text{ mA}$, $I_{B(on)} = -I_{B(off)} = 1 \text{ mA}$	—	480	800	ns

Ratings and Characteristic Curves

Fig. 1 Switching Waveforms

